SLLS213A - JANUARY 1996 - REVISED JUNE 1999

- Single Chip With Easy Interface Between **UART and Serial-Port Connector of an External Modem or Other Computer** Peripheral
- **Five Drivers and Three Receivers Meet or Exceed the Requirements of ANSI Standard** TIA/EIA-232-F and ITU Recommendation V.28 Standards
- Supports Data Rates up to 120 kbit/s
- Complement to the GD75232
- Provides Pin-to-Pin Replacement for the Goldstar GD75323
- **Pin-Out Compatible With SN75196**
- **Functional Replacement for the MC145405**

DW OR N PACKAGE (TOP VIEW) Vcc L 20 🛮 V_{DD} 1DA **∏** 2 19 1DY 2DA **∏** 3 18 2DY 3DA **∏** 4 17 **∏** 3DY 1RY **[**] 5 2RY [6 15 2RA 4DA **∏** 7 14**∏** 4DY 13 T 3RA 3RY [8 5DA **∏** 9 12 5DY GND **1** 10 11 [] V_{SS}

description

The GD75323 combines five drivers and three receivers from the trade-standard SN75188 and SN75189 bipolar quadruple drivers and receivers, respectively. The flow-through design of the GD75323 decreases the part count, reduces the board space required, and allows easy interconnection of the UART and serial-port connector. The all-bipolar circuits and processing of the GD75323 provide a rugged, low-cost solution for this function.

The GD75323 complies with the requirements of the ANSI TIA/EIA-232-F and ITU (formerly CCITT) V.28 standards. These standards are for data interchange between a host computer and a peripheral at signal rates up to 20 kbit/s. The switching speeds of the GD75323 are fast enough to support rates up to 120 kbit/s with lower capacitive loads (shorter cables). Interoperability at the higher signaling rates cannot be assured unless the designer has design control of the cable and the interface circuits at both ends. For interoperability at signaling rates up to 120 kbit/s, use of ANSI Standard TIA/EIA-423-B and TIA/EIA-422-B and ITU Recommendations V.10 and V.11 are recommended.

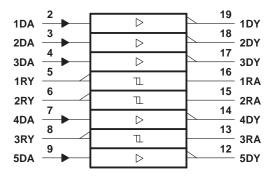
The GD75323 is characterized for operation over a temperature range of 0°C to 70°C.



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logic symbol[†]

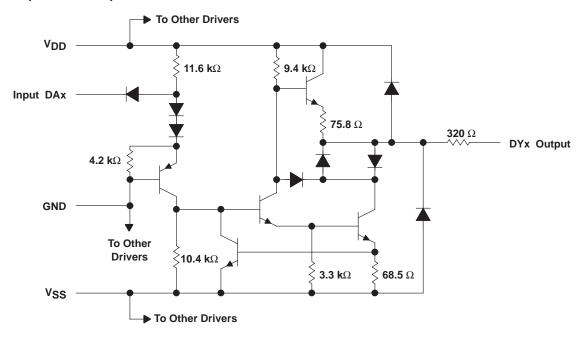


[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)

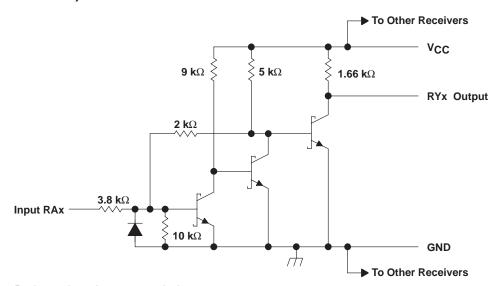


schematic (each driver)



Resistor values shown are nominal.

schematic (each receiver)



Resistor values shown are nominal.

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{CC} (see Note 1)	10 V
Supply voltage, V _{DD} (see Note 1)	
Supply voltage, V _{SS} (see Note 1)	
Input voltage range, V _I : Driver	
Receiver	30 V to 30 V
Output voltage range, VO (Driver)	– 15 V to 15 V
Low-level output current, IOL (Receiver)	20 mA
Package thermal impedance, θ _{JA} (see Note 2): DW package	97°C/W
N package	67°C/W
Lead temperature 1,6 mm (1/16 inch) from case for 10 second	ds 260°C
Storage temperature range, T _{stq}	– 65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

recommended operating conditions

		MIN	NOM	MAX	UNIT
	V_{DD}	7.5	9	13.5	
Supply voltage	V _{SS}	-7.5	-9	-13.5	V
	Vcc	4.5	5	5.5	
High-level input voltage, VIH	Driver	1.9			V
Low-level input voltage, V _{IL}	Driver			0.8	V
High level output ourrent leve	Driver			-6	mA
High-level output current, IOH	Receiver			-0.5	ША
High lovel output ourrent les	Driver			6	mA
High-level output current, IOL	Receiver			16	IIIA
Operating free-air temperature,TA		0		70	°C

supply currents over operating free-air temperature range

	PARAMETER		TEST CONDITIONS				MAX	UNIT
I _{DD} Supply current from V _{DD}	All inputs at 1.0 V	Nolood	$V_{DD} = 9 V$,	$V_{SS} = -9 V$		25	mA	
	All inputs at 1.9 V, No load		V _{DD} = 12 V,	$V_{SS} = -12 \text{ V}$		32	IIIA	
	All inputs at 0.8 V,	No load	V _{DD} = 9 V,	$V_{SS} = -9 V$		7.5	m /\	
	All inputs at 0.6 V, No load	V _{DD} = 12 V,	$V_{SS} = -12 \text{ V}$		9.5	mA		
		All inputs at 1.9 V,	No load	$V_{DD} = 9 V$,	$V_{SS} = -9 V$		-25	mA
las	Cupply ourront from Vaa			V _{DD} = 12 V,	$V_{SS} = -12 \text{ V}$		-32	IIIA
ISS Supply current from VSS	All innuts at 0.0 V	Natard	$V_{DD} = 9 V$,	V _{SS} = -9 V		-5.3	m A	
	All inputs at 0.8 V, No load		V _{DD} = 12 V,	$V_{SS} = -12 \text{ V}$		-5.3	mA	
ICC	Supply current from V _{CC}	V _{CC} = 5 V,	All inputs at 5 V,	No load			20	mA



NOTES: 1. All voltages are with respect to the network ground terminal.

^{2.} The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

DRIVER SECTION

electrical characteristics over operating free-air temperature range, V_{DD} = 9 V, V_{SS} = -9 V, V_{CC} = 5 V (unless otherwise noted)

	PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT	
Vон	High-level output voltage	$V_{IL} = 0.8 V,$	$R_L = 3 k\Omega$,	See Figure 1	6	7.5		V
VOL	Low-level output voltage (see Note 3)	V _{IH} = 1.9 V,	$R_L = 3 k\Omega$,	See Figure 1		-7.5	-6	V
lΗ	High-level input current	V _I = 5 V,	See Figure 2				10	μΑ
Iμ	Low-level input current	V _I = 0,	See Figure 2				-1.6	mA
IOS(H)	High-level short-circuit output current (see Note 4)	V _{IL} = 0.8 V,	V _O = 0,	See Figure 1	-4.5	-9	-19.5	mA
los(L)	Low-level short-circuit output current	V _{IH} = 2 V,	V _O = 0,	See Figure 1	4.5	9	19	mA
r _O	Output resistance (see Note 5)	VCC = VDD =	V _{SS} = 0,	$V_0 = -2 \text{ V to } 2 \text{ V}$	300			Ω

- NOTES: 3. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only, e.g., if –10 V is maximum, the typical value is a more negative voltage.
 - 4. Output short-circuit conditions must maintain the total power dissipation below absolute maximum ratings.
 - 5. Test conditions are those specified by TIA/EIA-232-F and as listed above.

switching characteristics, V_{DD} = 12 V, V_{SS} = -12 V, V_{CC} = 5 V $\pm 10\%$, T_A = 25°C

	PARAMETER	TEST CONDITI	TEST CONDITIONS		TYP	MAX	UNIT
^t PLH	Propagation delay time, low- to high-level output	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$	C _L = 15 pF,		315	500	ns
t _{PHL}	Propagation delay time, high- to low-level output	See Figure 3			75	175	ns
	Transition time law to high level output	R_L = 3 kΩ to 7 kΩ, See Figure 3	C _L = 15 pF,		60	100	ns
t _{TLH} Transition time, low- to high-level output	R_L = 3 kΩ to 7 kΩ, See Figure 3 and Note 6	$C_L = 2500 \text{ pF},$		1.7	2.5	μs	
Transition time, high- to low-level output (see tTHL Note 5)	R_L = 3 kΩ to 7 kΩ, See Figure 3	C _L = 15 pF,		40	75	ns	
	Note 5)	R_L = 3 kΩ to 7 kΩ, See Figure 3 and Note 7	$C_L = 2500 \text{ pF},$		1.5	2.5	μs

- NOTES: 6. Measured between 3-V and 3-V points of the output waveform (TIA/EIA-232-F conditions), all unused inputs are tied either high or low.
 - 7. Measured between 3-V and -3-V points of the output waveform (TIA/EIA-232-F conditions), all unused inputs are tied either high or low.



RECEIVER SECTION

electrical characteristics over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP [†]	MAX	UNIT
Vi- Regitive going input threehold voltage	Desitive going input threshold voltage	Can Figure 5	T _A = 25°C	1.75	1.9	2.3	
VIT+	Positive-going input threshold voltage	See Figure 5	T _A = 0°C to 70 °C	1.55		2.3	V
V _{IT} -	Negative-going input threshold voltage	Coo Figuro F		0.75	0.97	1.25	V
V _{hys}	Input hysteresis voltage (V _{IT+} - V _{IT-})	See Figure 5		0.5			
VOH High-level output voltage	High level output veltage	$I_{OH} = -0.5 \text{ mA}$	V _{IH} = 0.75 V	2.6	4	5	V
	High-level output voltage		Inputs open	2.6			
VOL	Low-level output voltage	$I_{OL} = 10 \text{ mA},$	V _I = 3 V		0.2	0.45	V
1	High-level input current	V _I = 25 V,	See Figure 5	3.6		8.3	mA
IH	right-level input current	V _I = 3 V,	See Figure 5	0.43			IIIA
1	Low-level input current	$V_{I} = -25 \text{ V},$ $V_{I} = -3 \text{ V},$	See Figure 5	-3.6		-8.3	A
¹IL			See Figure 5	-0.43			mA
los	Short-circuit output current	See Figure 4			-3.4	-12	mA

[†] All typical values are at $T_A = 25$ °C, $V_{CC} = 5$ V, $V_{DD} = 9$ V, and $V_{SS} = -9$ V.

switching characteristics, V_{CC} = 5 V, V_{DD} = 12 V, V_{SS} = -12 V, T_A = 25°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low- to high-level output	C _L = 50 pF,			107	500	ns
tPHL	Propagation delay time, high- to low-level output		$R_L = 5 k\Omega$,		42	150	ns
tTLH	Transition time, low- to high-level output	See Figure 6			175	525	ns
tTHL	Transition time, high- to low-level output				16	60	ns

PARAMETER MEASUREMENT INFORMATION

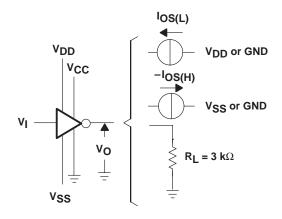


Figure 1. Driver Test Circuit for V_{OH} , V_{OL} , $I_{OS(H)}$, and $I_{OS(L)}$

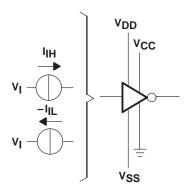
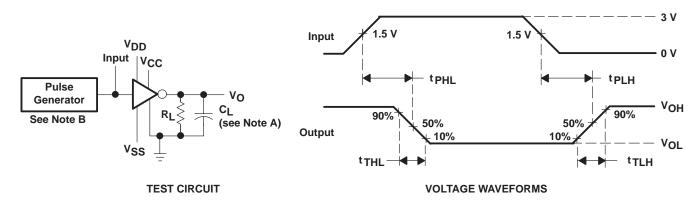


Figure 2. Driver Test Circuit for $I_{\mbox{\scriptsize IH}}$ and $I_{\mbox{\scriptsize IL}}$



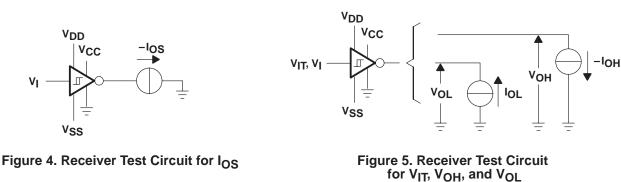
PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_I includes probe and jig capacitance.

B. The pulse generator has the following characteristics: t_W = 25 μ s, PRR = 20 kHz, Z_O = 50 Ω , t_r = t_f < 50 ns.

Figure 3. Driver Test Circuit and Voltage Waveforms



50% 50% Input V_{DD} -5 V Input ^tPHL ^tPLH **Pulse** ۷o Generator ۷он 90% See Note B (see Note A) 50% 50% Output 10% 10% Vol VSS tTHLtTLH **TEST CIRCUIT VOLTAGE WAVEFORMS**

NOTES: A. C_I includes probe and jig capacitance.

B. The pulse generator has the following characteristics: $t_W = 25 \,\mu s$, PRR = 20 kHz, $Z_O = 50 \,\Omega$, $t_T = t_f < 50 \,ns$.

Figure 6. Receiver Propagation and Transition Times

TYPICAL CHARACTERISTICS DRIVER SECTION

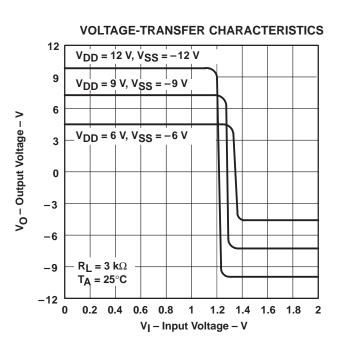


Figure 7

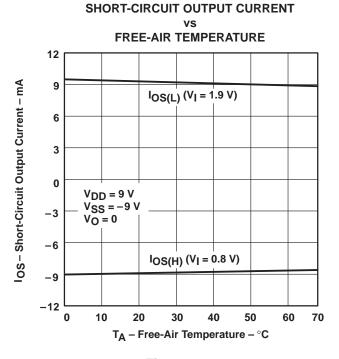


Figure 9

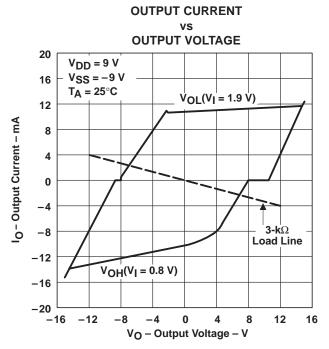


Figure 8

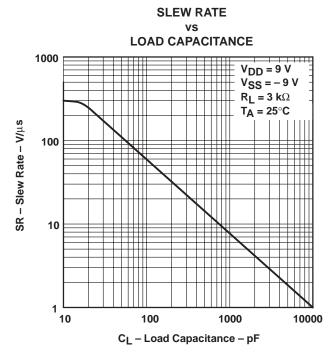
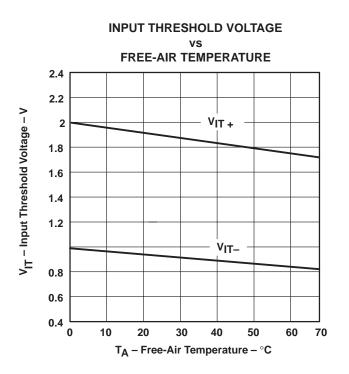


Figure 10



INPUT THRESHOLD VOLTAGE

TYPICAL CHARACTERISTICS RECEIVER SECTION



SUPPLY VOLTAGE 2 $V_{\text{IT+}}$ 1.8 V_{IT} - Input Threshold Voltage - V 1.6 1.4 1.2 1 V_{IT}-0.8 0.6 0.4 0.2 0 2 3 5 8 9 10 V_{CC} - Supply Voltage - V

Figure 11

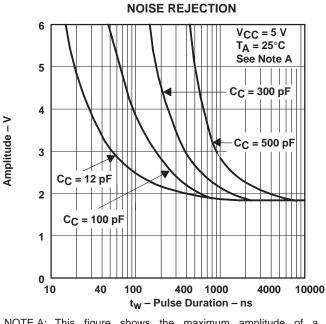
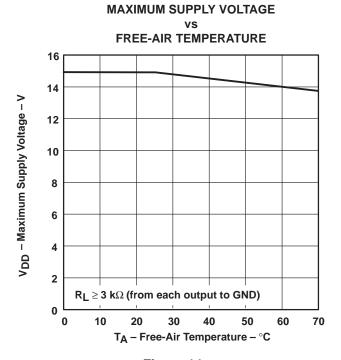


Figure 12



NOTE A: This figure shows the maximum amplitude of a positive-going pulse that, starting from 0 V, does not cause a change of the output level.

Figure 13

Figure 14



APPLICATION INFORMATION

Diodes placed in series with the V_{DD} and V_{SS} leads protect the GD75323 in the fault condition in which the device outputs are shorted to V_{DD} or V_{SS} , and the power supplies are at low and provide low-impedance paths to ground (see Figure 15).

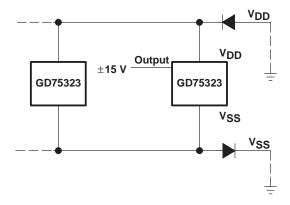
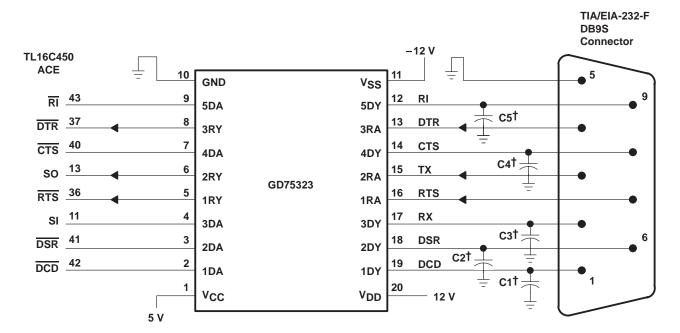


Figure 15. Power-Supply Protection to Meet Power-Off Fault Conditions of TIA/EIA-232-F



[†] See Figure 10 to select the correct values for the loading capacitors (C1, C2, C3, C4, and C5), which may be required to meet the RS-232 maximum slew-rate requirement of 30 V/μs. The value of the loading capacitors required depends upon the line length and desired slew rate, but is typically 330 pF.

NOTE C: To use the receivers only, $V_{\mbox{DD}}$ and $V_{\mbox{SS}}$ both must be powered or tied to ground.

Figure 16. Typical Connection



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